

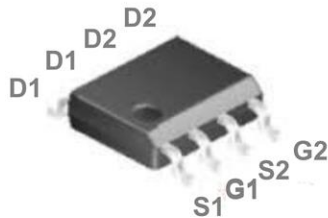
### Product Summary

- $V_{DS} = 40V$   $I_D = -8 A$
- $R_{DS(ON)} < -20m\Omega$  @  $V_{GS}=10 V$
- $R_{DS(ON)} < -25 m\Omega$  @  $V_{GS}=4.5V$

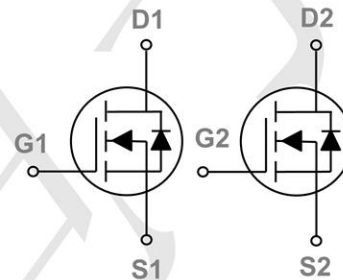
### Application

- DC-DC Converters.
- Load Switch.
- Power Management.

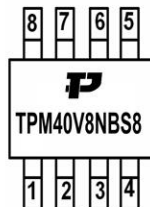
### Package and Pin Configuration



### Circuit diagram



### Marking:



### Absolute Maximum Ratings $T_c=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $T_A=25^\circ C$ )	8	A
	Drain Current – Continuous ( $T_A=70^\circ C$ )	6.4	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	32	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	4.9	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	9.9	A
$P_D$	Power Dissipation ( $T_A=25^\circ C$ )	2	W
	Power Dissipation – Derate above $25^\circ C$	0.016	W/ $^\circ C$
$T_{STG}$	Storage Temperature Range	-50 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-50 to 150	$^\circ C$

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62.5	$^\circ C/W$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	---	---	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =32V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =8A	---		20	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A	---		25	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.6	2.5	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =1A	---	5	---	S

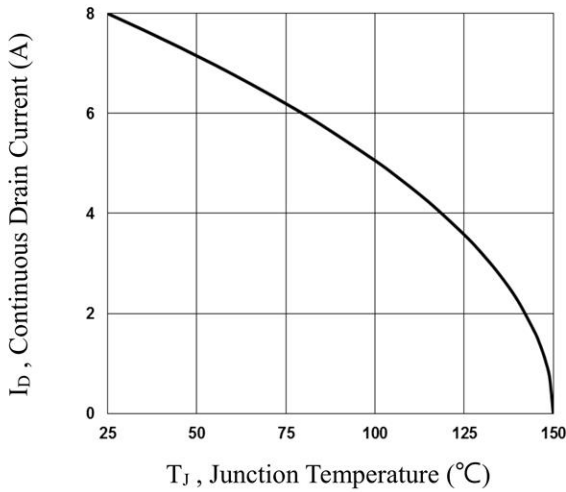
**Dynamic and switching Characteristics**

Q <sub>g</sub>	Total Gate Charge <sup>2,3</sup>	V <sub>DS</sub> =32V, V <sub>GS</sub> =10V, I <sub>D</sub> =3A	---	10.8	21.6	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>2,3</sup>		---	1.6	3.2	
Q <sub>gd</sub>	Gate-Drain Charge <sup>2,3</sup>		---	3.3	6.6	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2,3</sup>	V <sub>DD</sub> =15V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω I <sub>D</sub> =1A	---	3.8	7.6	ns
T <sub>r</sub>	Rise Time <sup>2,3</sup>		---	10.5	21	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>2,3</sup>		---	22.2	45	
T <sub>f</sub>	Fall Time <sup>2,3</sup>		---	6.6	13.2	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, F=1MHz	---	724	1450	pF
C <sub>oss</sub>	Output Capacitance		---	70	140	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	109	220	
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	---	2.6	---	Ω

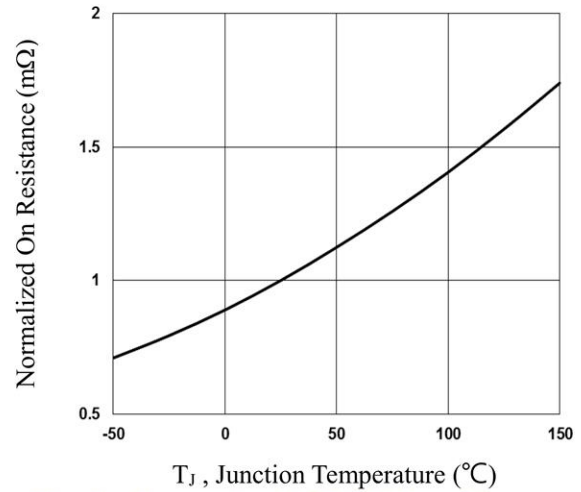
**Drain-Source Diode Characteristics and Maximum Ratings**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	8	A
I <sub>SM</sub>	Pulsed Source Current		---	---	16	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V

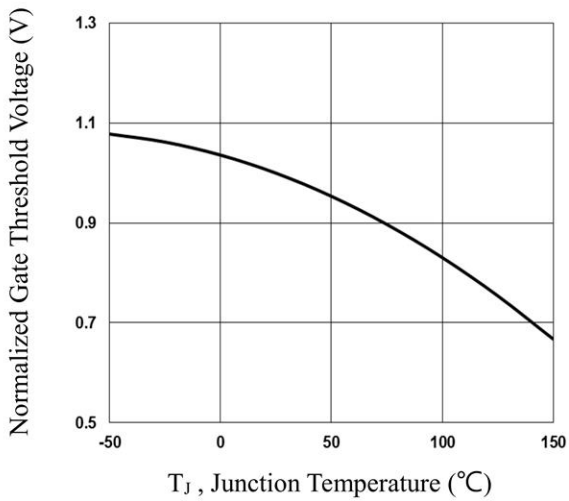
**Typical Performance Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise Specified)**



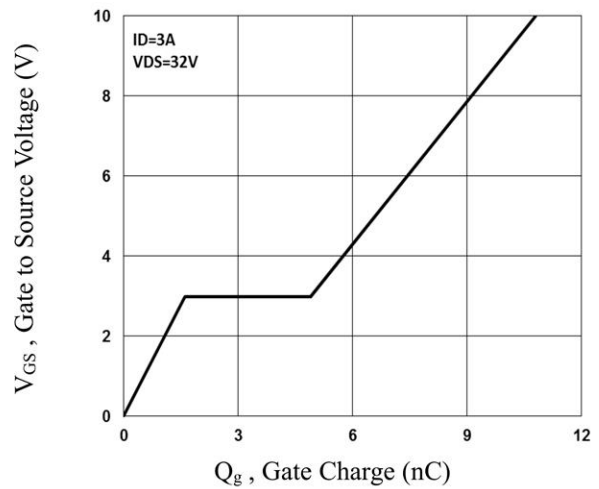
**Fig.1 Continuous Drain Current vs.  $T_c$**



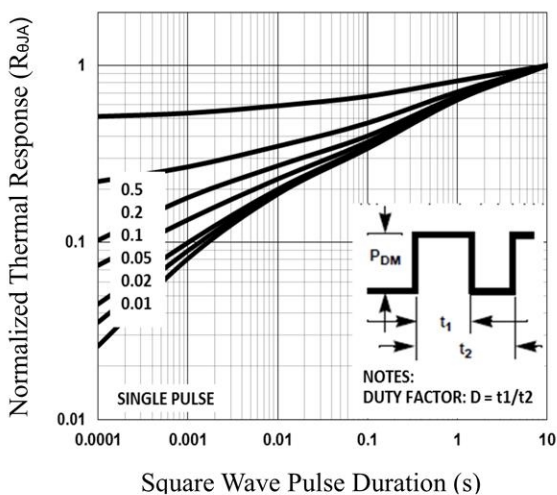
**Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_j$**



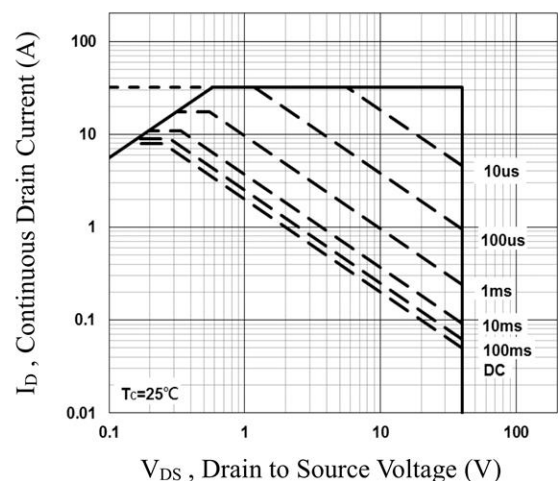
**Fig.3 Normalized  $V_{th}$  vs.  $T_j$**



**Fig.4 Gate Charge Waveform**

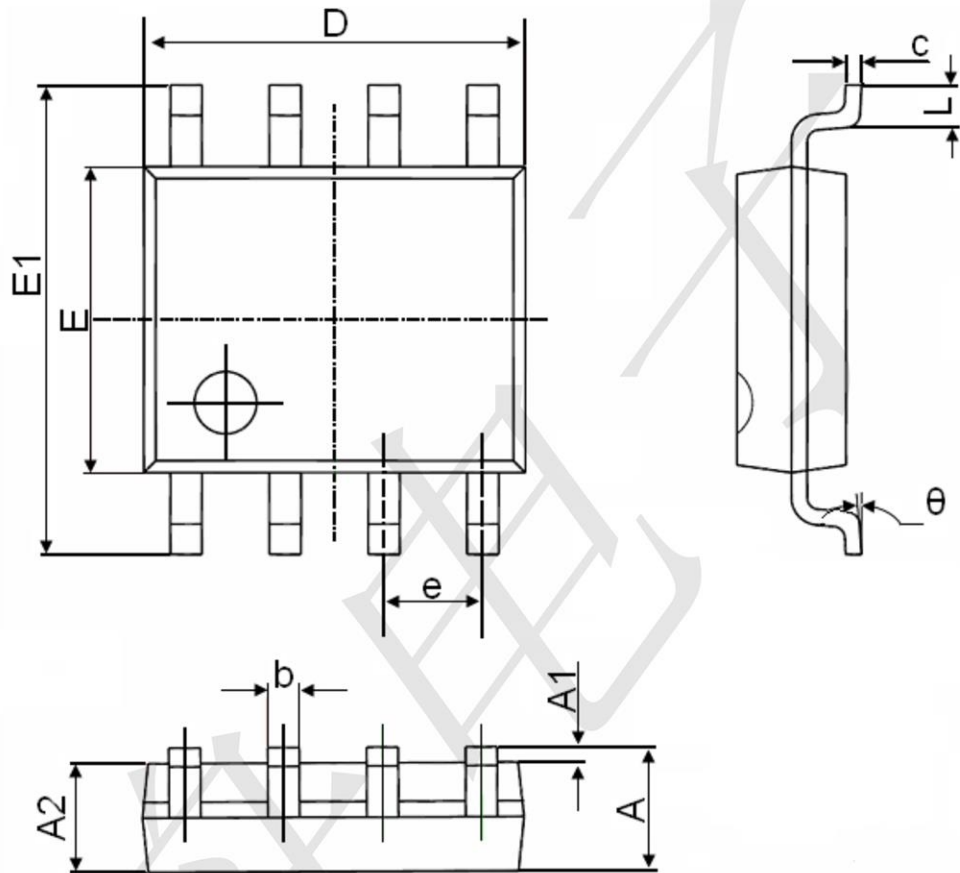


**Fig.5 Normalized Transient Impedance**



**Fig.6 Maximum Safe Operation Area**

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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